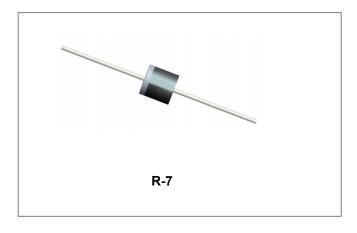


# ST3045AX-D ST3045AX-C

Technical Data Data Sheet N2413, Rev. B



# ST3045AX-D/ST3045AX-C SCHOTTKY BARRIER RECTIFIER



## **Circuit Diagram**



# Features

- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Trench MOS Schottky technology
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Mechancal Data**

- Case: R-7 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any

## Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	45	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=120°C, In DC	30	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	350	А

# **Electrical Characteristics:**

Characteristics	Cumhal	Condition	Tum	May	L lusite
Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 30A, Pulse, T <sub>J</sub> = 25 °C	0.49	0.55	V
Reverse Current*	I <sub>R1</sub>	$@V_R$ = rated $V_{R, T_J}$ = 25 °C	0.02	0.2	mA
	I <sub>R2</sub>	$@V_R = rated V_{R,} T_J = 100 \ ^{\circ}C$	-	20	mA
Junction Capacitance	Ст	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz	3680	-	pF

\* Pulse width < 300 μs, duty cycle < 2%

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# ST3045AX-D ST3045AX-C

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# Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	In DC Forward Mode, without reverse bias, t ≤1 hour	-55 to +200	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance	R <sub>0JC</sub>	DC operation	1.8	°C/W
Annexine etc. M/sight		ST3045AX-D	2.6	
Approximate Weight	wt	ST3045AX-C	3	g
Case Style		R-7		

# **Ratings and Characteristics Curves**

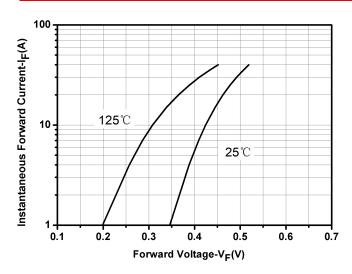


Fig.1-Typical Forward Voltage Characteristics

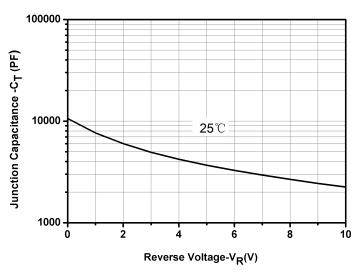
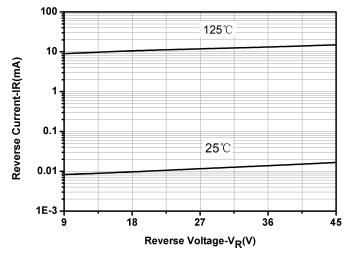


Fig.3-Capacitance vs. Reverse Voltage



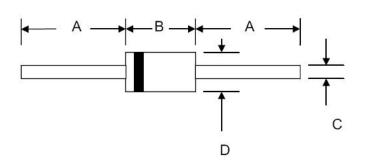
**Fig.2-Typical Reverse Characteristics** 





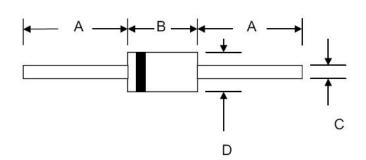


# Mechanical Dimensions R-7(ST3045AX-D)



SYMBOL	Millimeters		Inches		
STMBOL	Min.	Max.	Min.	Max.	
А	15.00	-	0.590	-	
В	8.60	9.10	0.340	0.360	
С	1.90	2.10	0.075	0.083	
D	8.60	9.10	0.340	0.360	

## Mechanical Dimensions R-7(ST3045AX-C)



SYMBOL	Millin	neters	Inches		
STMBOL	Min.	Max.	Min.	Max.	
А	24.5	-	0.965	-	
В	8.60	9.10	0.340	0.360	
С	1.90	2.10	0.075	0.083	
D	8.60	9.10	0.340	0.360	

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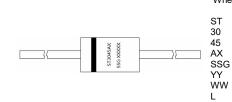


## **Ordering Information**

Device	Package	Shipping
ST3045AX-D	R-7(Pb-Free)	800pcs / reel
ST3045AX-C	R-7(Pb-Free)	800pcs / reel
ST3045AX-DTR	R-7(Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

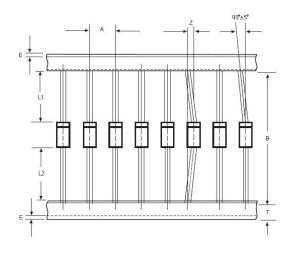
# Marking Diagram



Where XXXXX is YYWWL

- = Device Type
- = Forward Current (30A)
- = Reverse Voltage (45V)
- = Package type = SSG
  - = Year
  - = Week
  - = Lot Number

# **Carrier Tape Specification R-7**



SYMBOL	Millimeters		
STNIBOL	Min.	Max.	
А	9.50	10.50	
В	50.9	53.9	
Z	-	1.20	
Т	5.60	6.40	
E	-	0.80	
IL1-L2I	-	1.0	





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